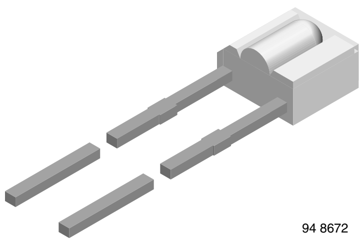
Infrared Emitting Diode, RoHS Compliant, 950 nm, GaAs


94 8672

FEATURES

- Package type: leaded
- Package form: side view
- Dimensions (L x W x H in mm): 3.6 x 2.2 x 5
- Peak wavelength: λ_p = 950 nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity: φ = ± 25°, horizontal
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Package matched with detector TEST2600
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC

Pb-free
e2
RoHS COMPLIANT

DESCRIPTION

TSSS2600 is an infrared, 950 nm emitting diode in GaAs technology, molded in a miniature, clear plastic package with side view lens.

APPLICATIONS

- Infrared source in miniature light barriers or reflective sensor systems with short transmission distances and low forward voltage requirements. Matching with silicon PIN photodiodes or phototransistors (e.g. TEST2600)

PRODUCT SUMMARY

COMPONENT	I_e (mW/sr)	φ (deg)	λ_p (nm)	t_r (ns)
TSSS2600	2.6	± 25	950	800

Note
Test conditions see table “Basic Characteristics”

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSSS2600	Bulk	MOQ: 5000 pcs, 5000 pcs/bulk	Side view

Note
MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	5	V
Forward current		I_F	100	mA
Peak forward current	$t_p/T = 0.5$, t_p = 100 µs	I_{FM}	200	mA
Surge forward current	t_p = 100 µs	I_{FSM}	2.0	A
Power dissipation		P_V	170	mW
Junction temperature		T_j	100	°C
Operating temperature range		T_{amb}	- 40 to + 100	°C
Storage temperature range		T_{stg}	- 40 to + 100	°C
Soldering temperature	t ≤ 5 s, 2 mm from case	T_{sd}	260	°C
Thermal resistance junction/ambient	Leads not soldered	R_{thJA}	450	K/W

Note
T_{amb} = 25 °C, unless otherwise specified

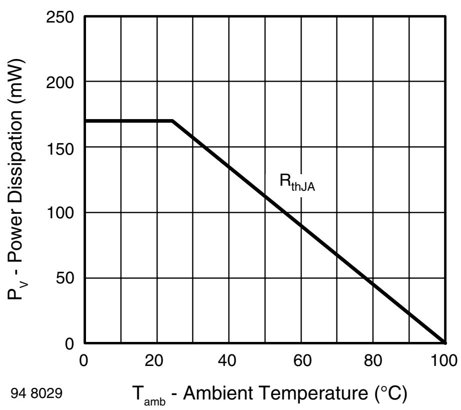


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

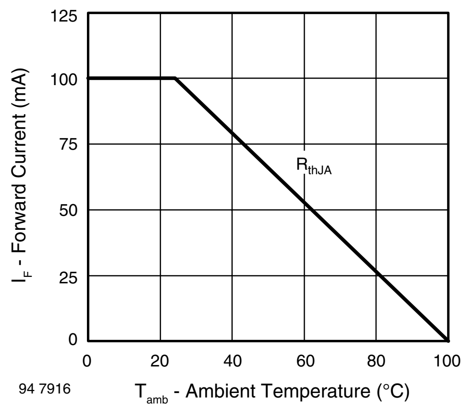


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I_F = 100 mA, t_p = 20 ms	V_F		1.25	1.6	V
	I_F = 1.5 A, t_p = 100 µs	V_F		2.2		V
Temperature coefficient of V_F	I_F = 100 mA	TK_{VF}		- 1.3		mV/K
Reverse current	V_R = 5 V	I_R			100	µA
Junction capacitance	V_R = 0 V, f = 1 MHz, E = 0	C_j		30		pF
Radiant intensity	I_F = 100 mA, t_p = 20 ms	I_e	1	2.6	3	mW/sr
	I_F = 1.5 A, t_p = 100 µs	I_e		25		mW/sr
Radiant power	I_F = 100 mA, t_p = 20 ms	ϕ_e		20		mW
Temperature coefficient of ϕ_e	I_F = 100 mA	$TK\phi_e$		- 0.8		%/K
Angle of half intensity	horizontal	φ_1		± 25		deg
	vertical	φ_2		± 60		deg
Peak wavelength	I_F = 100 mA	λ_p		950		nm
Spectral bandwidth	I_F = 100 mA	$\Delta\lambda$		50		nm
Temperature coefficient of λ_p	I_F = 100 mA	$TK\lambda_p$		0.2		nm/K
Rise time	I_F = 100 mA	t_r		800		ns
	I_F = 1.5 A	t_r		400		ns
Fall time	I_F = 100 mA	t_f		800		ns
	I_F = 1.5 A	t_f		400		ns
Virtual source diameter		d		2		mm

Note

T_{amb} = 25 °C, unless otherwise specified

BASIC CHARACTERISTICS

T_{amb} = 25 °C, unless otherwise specified

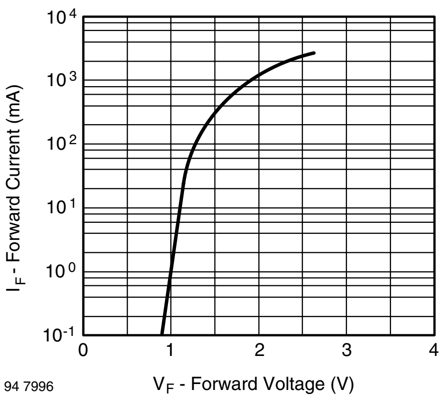


Fig. 3 - Pulse Forward Current vs. Forward Voltage

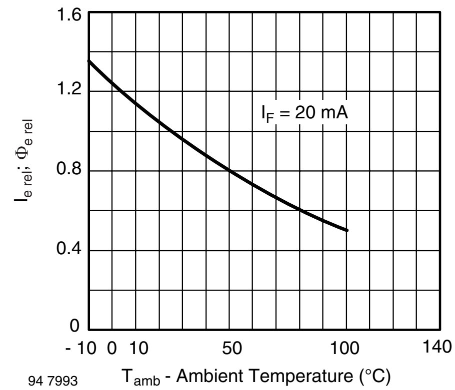


Fig. 6 - Relative Radiant Intensity/Power vs. Ambient Temperature

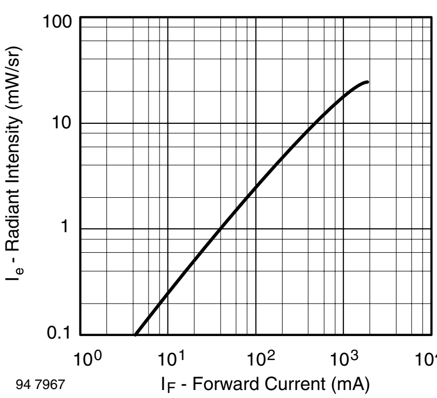


Fig. 4 - Radiant Intensity vs. Forward Current

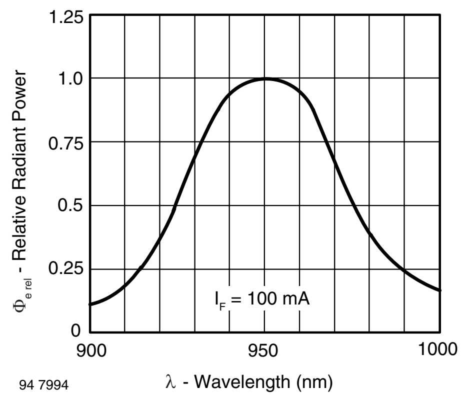


Fig. 7 - Relative Radiant Power vs. Wavelength

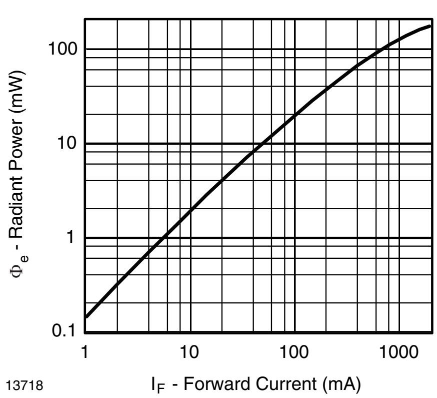


Fig. 5 - Radiant Power vs. Forward Current

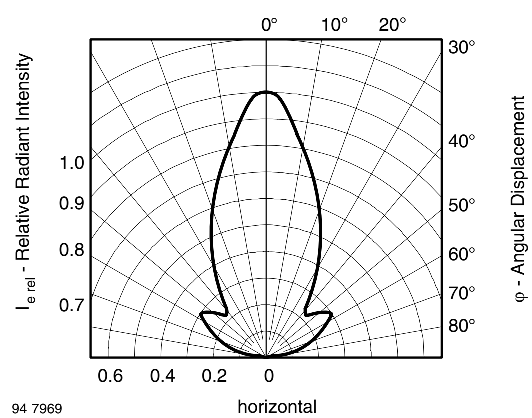


Fig. 8 - Relative Radiant Intensity vs. Angular Displacement

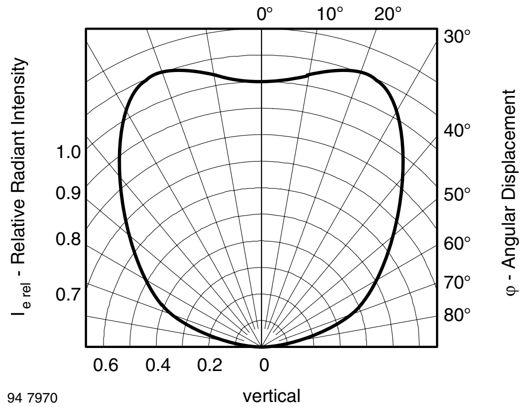
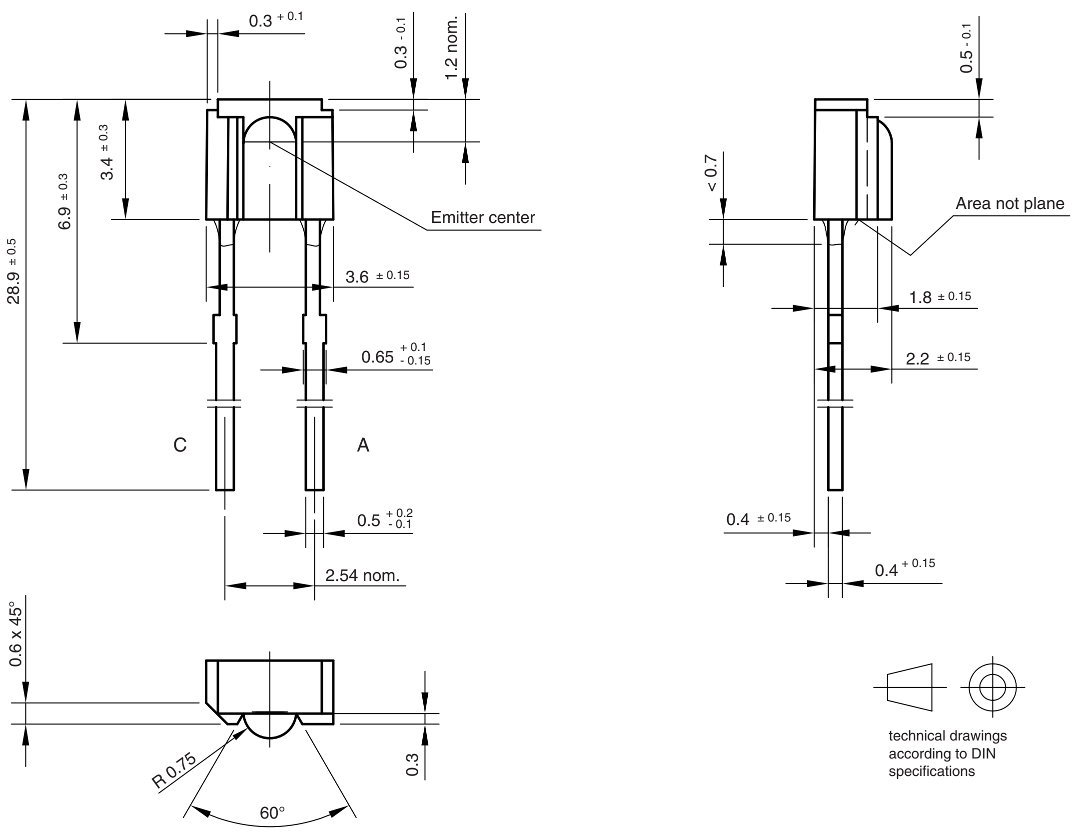


Fig. 9 - Relative Radiant Intensity vs. Angular Displacement

PACKAGE DIMENSIONS in millimeters



Drawing-No.: 6.544-5241.01-4
Issue: 3; 18.04.96
95 11488

Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, “Vishay”), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay’s terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.